


DMP2305U

P-CHANNEL ENHANCEMENT MODE MOSFET

Features

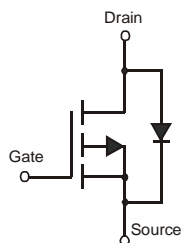
- Low On-Resistance
 - 60mΩ @ $V_{GS} = -4.5V$
 - 90mΩ @ $V_{GS} = -2.5V$
 - 113mΩ @ $V_{GS} = -1.8V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

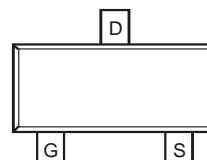
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)



Top View



Internal Schematic



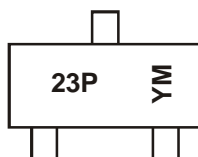
Top View

Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMP2305U-7	Commercial	SOT23	3000/Tape & Reel
DMP2305UQ-7	Automotive	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Marking Information



23P = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: W = 2009)
 M = Month (ex: 9 = September)

Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015
Code	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	± 8	V
Continuous Drain Current (Note 5)	Steady State	$T_A = 25^\circ\text{C}$	I_D	-4.2	A
		$T_A = 70^\circ\text{C}$		-3.4	
Pulsed Drain Current (Note 6)			I_{DM}	-10	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	1.4	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	90	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	-	-0.9	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	45	60	m Ω	$V_{GS} = -4.5V, I_D = -4.2A$
			60	90		$V_{GS} = -2.5V, I_D = -3.4A$
			87	113		$V_{GS} = -1.8V, I_D = -2.0A$
Forward Transfer Admittance	$ Y_{fs} $	—	9	—	S	$V_{DS} = -5V, I_D = -4A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	727	—	pF	$V_{DS} = -20V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	69	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	64	—	pF	
Gate Resistance	R_G	—	23	—	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0\text{MHz}$
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_g	—	7.6	—	nC	$V_{GS} = -4.5V, V_{DS} = -4V, I_D = -3.5A$
Gate-Source Charge	Q_{gs}	—	1.4	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.2	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	14.0	—	ns	$V_{DS} = -4V, V_{GS} = -4.5V,$ $R_L = 4\Omega, R_G = 6\Omega, I_D = -1A$
Turn-On Rise Time	t_r	—	13.0	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	53.8	—	ns	
Turn-Off Fall Time	t_f	—	23.2	—	ns	

- Notes:
- Device mounted on FR-4 PCB with 2oz. Copper and test pulse width $t \leq 10s$.
 - Repetitive rating, pulse width limited by junction temperature.
 - Short duration pulse test used to minimize self-heating effect.